

ARTICLE

Electronic Supplementary Information

Boosted carrier mobility and enhanced thermoelectric properties of polycrystalline $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se}$ by liquid-phase hot deformation

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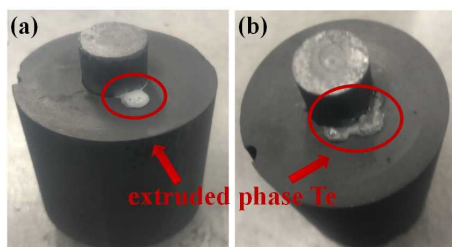


Fig. S1. Pictures of graphite dies after liquid-phase hot deformation for (a) $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se-5\%Te}$; (b) $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se-15\%Te}$.

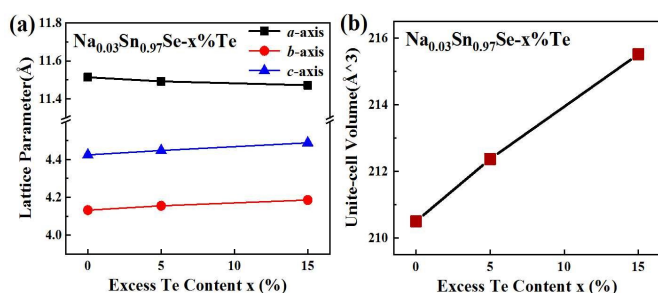


Fig. S2. Pictures of graphite dies after liquid-phase hot deformation for (a) $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se-5\%Te}$; (b) $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se-15\%Te}$.

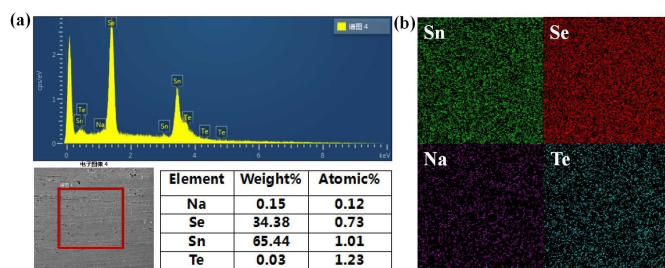


Fig. S3. The $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se-5\%Te}$ sample of (a) EDS spectrum taken from the red scanning area; (b) the elemental mapping of Sn, Se, Na and Te in the selected area.

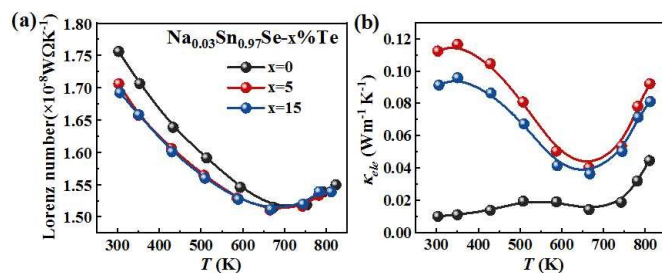


Fig. S4. $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se-x\%Te}$ samples of (a) Lorenz numbers;¹ (b) electronic thermal conductivity as a function of temperature.

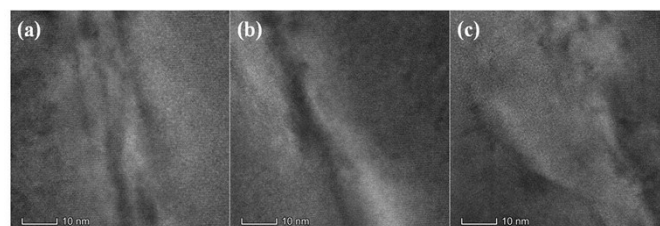


Fig. S5. HRTEM images of strain-field images from different areas in the $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se-5\%Te}$ sample.

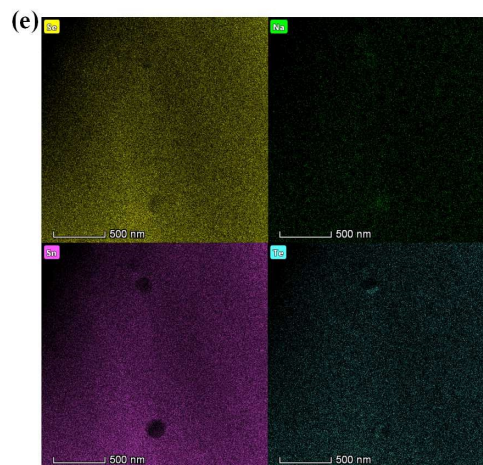
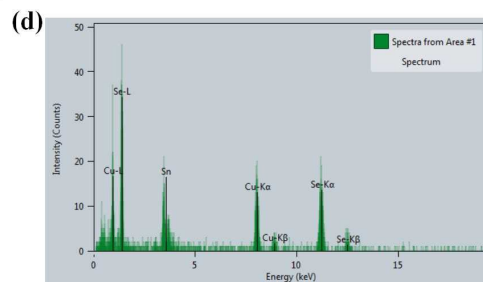
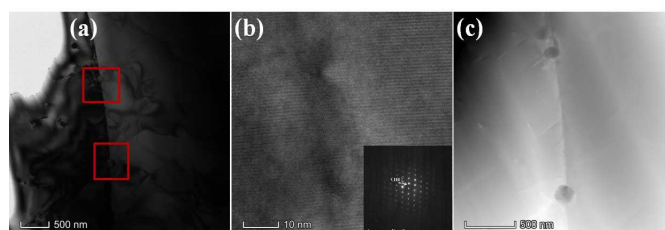


Fig. S6. Microstructure of the $\text{Na}_{0.03}\text{Sn}_{0.97}\text{Se}-5\%\text{Te}$ sample: (a) Low-magnification TEM image where Se-rich and Sn-poor precipitates in the red boxes; (b) HRTEM image from (a) region with its electron diffraction pattern; (c) HAADF-STEM image taken from the entire area of (b); (d) the corresponding EDS results for the areas with the composition of each given in atomic percentage; (e) EDS elemental maps. The interface regions were selenium precipitates and SnSe_2 second phase.^{2,3,4}

Table S1. The relative elemental content shown in Fig. S6d.

| | Atomic (%) | Atomic error (%) | Mass (%) | Mass error (%) | Fit error (%) |
|----|------------|------------------|----------|----------------|---------------|
| Se | 74.93 | 8.59 | 66.23 | 5.54 | 1.37 |
| Sn | 25.07 | 3.73 | 33.77 | 4.27 | 1.74 |
| Te | 0 | 0.33 | 0 | 0.46 | 0 |

References

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